

PRM8R5P03N3

PFC Device Corporation

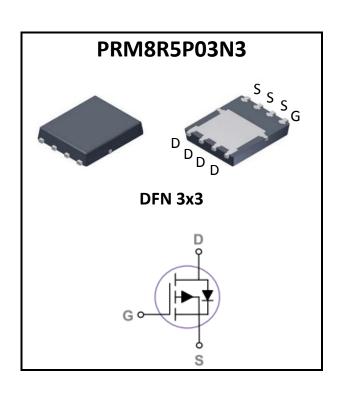
30V Single P-Channel MOSFET

Major ratings and characteristics

Characteristics	Values	Units
V_{DS}	-30	٧
$I_{D}^{3} (T_{C}=25^{\circ}C)$	-50	Α
Max.R _{DS(ON)} @V _{GS} =-10V	8.5	mΩ
T _J Operating Junction Temperature	-50 to +150	°C

General Description

The P-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.



Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting

Features

- Max. R_{DS(ON)}=8.5mΩ@V_{GS}=-10V
- Improved dv/dt capability
- Fast switching
- 100% E_{AS} Guaranteed
- Green Device Available

1. Characteristics

Maximum Ratings Characteristics

($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D^3	Drain Current – Continuous (T _C =25°C)	-50	А
ID	Drain Current – Continuous (T _C =100°C)	-32	А
I _{DM}	Drain Current – Pulsed ¹	-200	А
	Power Dissipation (T _C =25°C)	59	W
P_D	Power Dissipation – Derate above 25°C	0.47	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction to Case		2.1	°C/W



Version 4.1 2 / 7

Electrical Characteristics

($T_J = 25$ °C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30			V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V, T _J =25°C			-1	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V$, $V_{DS}=0V$			±100	nA

On Characteristics

R _{DS(ON)} Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-10A			8.5	mΩ	
$R_{DS(ON)}$	Static Dialii-Source Off-Resistance	V_{GS} =-4.5V, I_{D} =-8A		-	14	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=-250uA$	-1.0	-	-2.5	V
g fs	Forward Transconductance	V_{DS} =-10V, I_{D} =-5A		32		S

Dynamic and switching Characteristics

		1			1
Q_{g}	Total Gate Charge ²		 52		
Q_gs	Gate-Source Charge ²	V _{DS} =-20V, V _{GS} =-10V, I _D =-10A	 8.5		nC
Q_gd	Gate-Drain Charge ²		 9.5		
$T_{d(on)}$	Turn-On Delay Time ²		 10		
T_r	Turn-On Rise Time ²	V_{DD} =-15V, V_{GS} =-10V, R_{G} =6 Ω	 21.4		ns
$T_{d(off)}$	Turn-Off Delay Time ²	I _D =-1A	 95.6		113
T_f	Turn-Off Fall Time ²		 55		
C_{iss}	Input Capacitance		 3110		
C _{oss}	C _{oss} Output Capacitance V _{DS} =-15V, V _{GS} =0V, f=1MHz		 394		pF
C _{rss}	Reverse Transfer Capacitance		 247		
R_{g}	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	 5.5	1	Ω

Drain-Source Diode Characteristics

V	SD ³ Source	to Drain Diode Voltage	V _{GS} =0V, I _S =-1A			-1	V
---	------------------------	------------------------	--	--	--	----	---

Note:

- ${\bf 1.} \ \ {\bf Repetitive} \ {\bf Rating: Pulsed} \ {\bf width} \ {\bf limited} \ {\bf by} \ {\bf maximum} \ {\bf junction} \ {\bf temperature.}$
- 2. The data tested by pulsed, pulse width \leq 300us, duty cycle \leq 2%.
- 3. Silicon limited.



Version 4.1 3 / 7

2. Characteristics Curves

Ratings and Characteristics Curves

(T_A = 25°C unless otherwise specified)

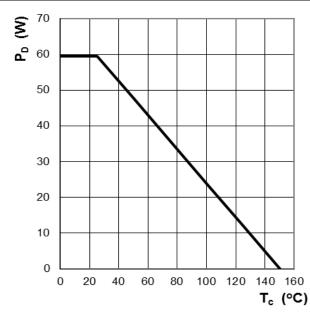


Figure 1: Power Dissipation

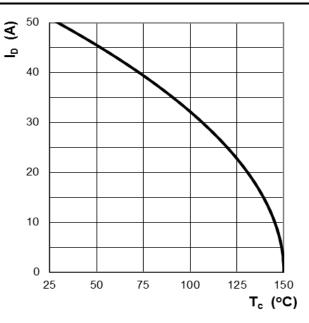


Figure 2: Continuous Drain Current vs. T_C

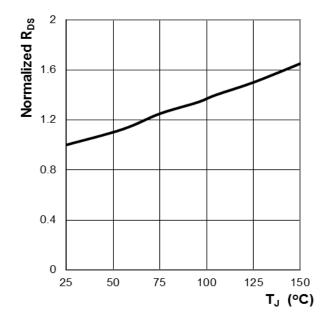


Figure 3: Normalized R_{DS(ON)} vs. T_J

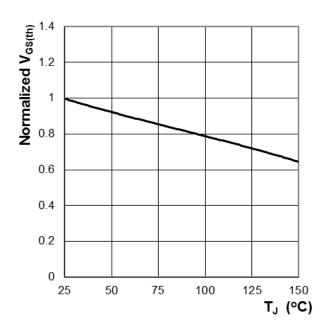


Figure 4: Normalized Vth vs. TJ



Version 4.1 4 / 7

Ratings and Characteristics Curves

($T_A = 25^{\circ}C$ unless otherwise specified)

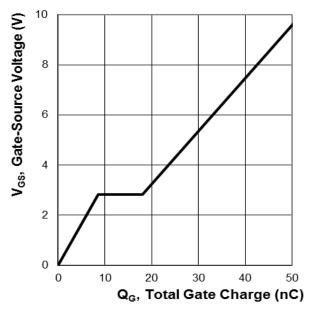


Figure 5: Typ. Gate Charge Characteristics

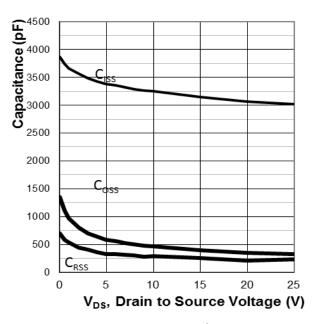


Figure 6: Typ. Capacitance Characteristics

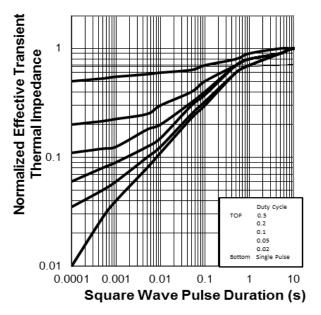


Figure 7: Normalized Thermal Transient Impedance, Junction-to-Case

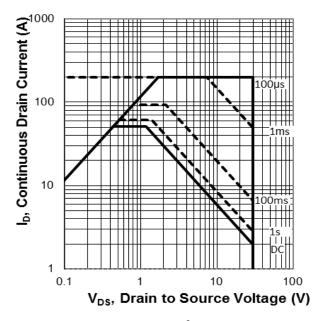


Figure 8: Maximum Safe Operation Area



Version 4.1 5 / 7

3. Marking information

Top Marking Rule

PFC PRM 8R5P03 YM ABS PRM8R5P03 = Product Type Marking Code

YM = Date Code

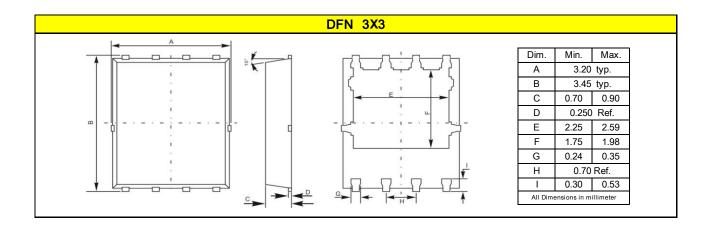
Y = Year code

M = Month code

ABS = Assembly code

4. Package information

Package Outline Dimensions millimeters





Version 4.1 6 / 7

5. Ordering information

Part Number	Package	Delivery mode
PRM8R5P03N3	DFN 3X3	5000 pcs / 13" diameter reel

Mechanical

Molder Plastic: UL Flammability Classification Rating 94V-0
Device Weight: 0.0025 ounces (0.072grams) – DFN 3X3

PFC Device Corp reserves the right to make changes without further notice to any products herein. PFC Device Corp makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does PFC Device Corp assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in PFC Device Corp data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" must be validated for each customer application by customer's technical experts. PFC Device Corp does not convey any license under its patent rights nor the rights of others. PFC Device Corp products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the PFC Device Corp product could create a situation where personal injury or death may occur. Should Buyer purchase or use PFC Device Corp products for any such unintended or unauthorized application, Buyer shall indemnify and hold PFC Device Corp and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that PFC Device Corp. was negligent regarding the design or manufacture of the part.



Version 4.1 7 / 7